

Medium Power Thyristors (Stud Version), 16 A



TO-208AA (TO-48)

FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High di/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- RoHS compliant
- Designed and qualified for industrial and consumer level



PRODUCT SUMMARY

$I_{T(AV)}$	16 A
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TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		16	A
	T_C	85	°C
$I_{T(RMS)}$		35	A
I_{TSM}	50 Hz	340	A
	60 Hz	360	
I^2t	50 Hz	574	A ² s
	60 Hz	524	
V_{DRM}/V_{RRM}		100 to 1200	V
t_q	Typical	110	µs
T_J		- 65 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
16RIA	10	100	150	20
	20	200	300	10
	40	400	500	
	60	600	700	
	80	800	900	
	100	1000	1100	
	120	1200	1300	

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if di/dt does not exceed 20 A/ μ s

⁽²⁾ For voltage pulses with $t_p \leq 5$ ms

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS	
Maximum average on-state current at case temperature	I _{T(AV)}	180° sinusoidal conduction			16	A	
					85	°C	
Maximum RMS on-state current	I _{T(RMS)}				35	A	
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	340	A	
		t = 8.3 ms			360		
		t = 10 ms	100 % V _{RRM} reapplied		285		
		t = 8.3 ms			300		
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		574	A ² s	
		t = 8.3 ms			524		
		t = 10 ms	100 % V _{RRM} reapplied		405		
		t = 8.3 ms			375		
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied, T _J = T _J maximum			5740	A ² √s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)} < I < π × I _{T(AV)}), T _J = T _J maximum			0.97	V	
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			1.24		
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)} < I < π × I _{T(AV)}), T _J = T _J maximum			17.9	mΩ	
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			13.6		
Maximum on-state voltage	V _{TM}	I _{pk} = 50 A, T _J = 25 °C			1.75	V	
Maximum holding current	I _H	T _J = 25 °C, anode supply 6 V, resistive load			130	mA	
Latching current	I _L				200		

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SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum rate of rise of turned-on current	di/dt	T _J = T _J maximum, V _{DM} = Rated V _{DRM} Gate pulse = 20 V, 15 Ω, t _p = 6 μs, t _r = 0.1 μs maximum I _{TM} = (2 x rated di/dt) A	200	A/μs
			180	
			160	
			150	
Typical turn-on time	t _{gt}	T _J = 25 °C, at rated V _{DRM} /V _{RRM} , T _J = 125 °C	0.9	μs
Typical reverse recovery time	t _{rr}	T _J = T _J maximum, I _{TM} = I _{T(AV)} , t _p > 200 μs, di/dt = - 10 A/μs	4	
Typical turn-off time	t _q	T _J = T _J maximum, I _{TM} = I _{T(AV)} , t _p > 200 μs, V _R = 100 V, di/dt = - 10 A/μs, dV/dt = 20 V/μs linear to 67 % V _{DRM} , gate bias 0 V to 100 W	110	

Note

- t_q = 10 μs up to 600 V, t_q = 30 μs up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 100 % rated V _{DRM}	100	V/μs
		T _J = T _J maximum linear to 67 % rated V _{DRM}	300 ⁽¹⁾	

Note

- ⁽¹⁾ Available with: dV/dt = 1000 V/μs, to complete code add S90 i.e. 16RIA120S90

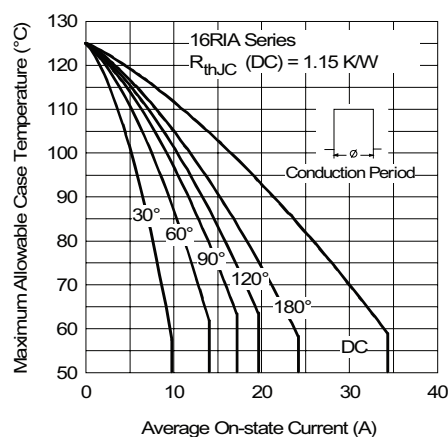
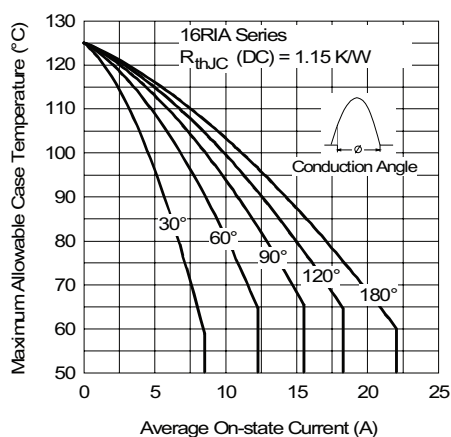
TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	T _J = T _J maximum	8.0	W
Maximum average gate power	P _{G(AV)}		2.0	
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum	1.5	A
Maximum peak negative gate voltage	-V _{GM}	T _J = T _J maximum	10	V
DC gate current required to trigger	I _{GT}	T _J = - 65 °C	90	mA
		T _J = 25 °C	60	
		T _J = 125 °C	35	
DC gate voltage required to trigger	V _{GT}	T _J = - 65 °C	3.0	V
		T _J = 25 °C	2.0	
		T _J = 125 °C	1.0	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated value	2.0	mA
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum, V _{DRM} = Rated value	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction and storage temperature range	T_J, T_{Stg}		- 65 to 125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.86	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.35	
			TO NUT	TO DEVICE
Mounting torque		Lubricated threads (Non-lubricated threads)	20 (27.5)	25
			0.23 (0.32)	0.29
			2.3 (3.1)	2.8
Approximate weight			14	g
			0.49	oz.
Case style		See dimensions - link at the end of datasheet	TO-208AA (TO-48)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.21	0.15	$T_J = T_J \text{ maximum}$	K/W
120°	0.25	0.25		
90°	0.31	0.34		
60°	0.45	0.47		
30°	0.76	0.76		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



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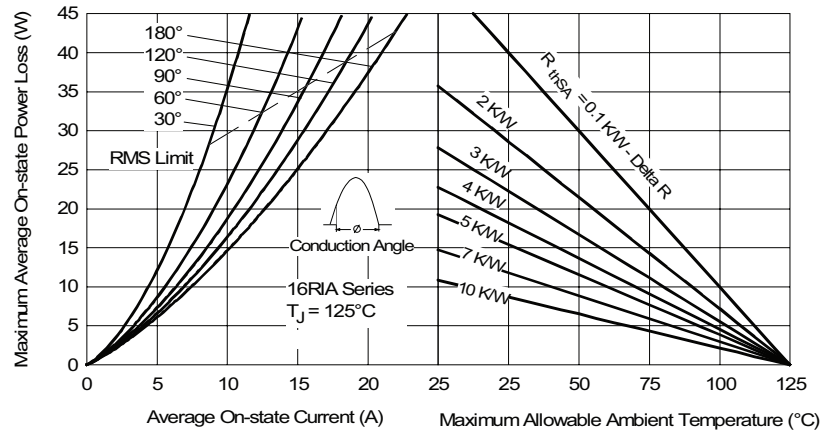


Fig. 3 - On-State Power Loss Characteristics

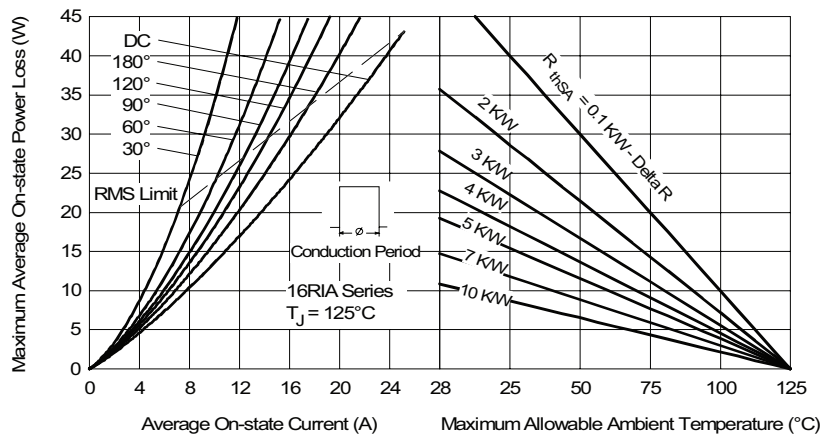


Fig. 4 - On-State Power Loss Characteristics

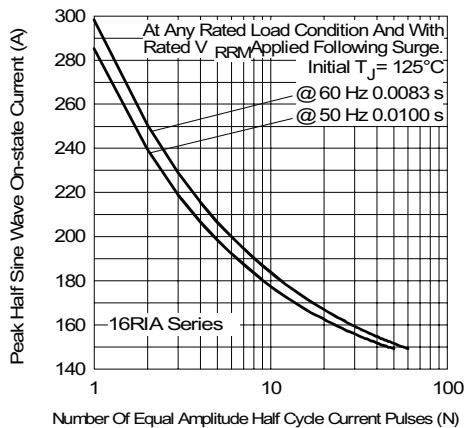


Fig. 5 - Maximum Non-Repetitive Surge Current

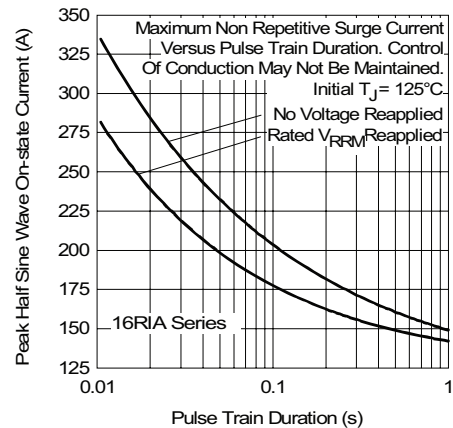


Fig. 6 - Maximum Non-Repetitive Surge Current

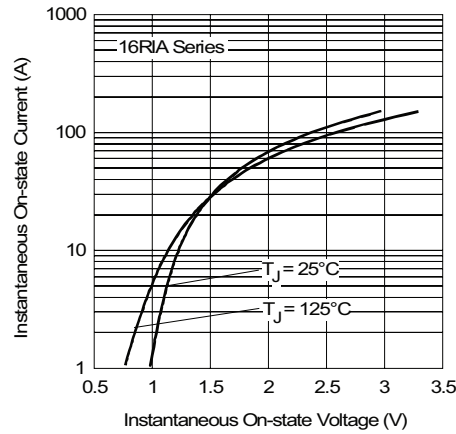


Fig. 7 - Forward Voltage Drop Characteristics

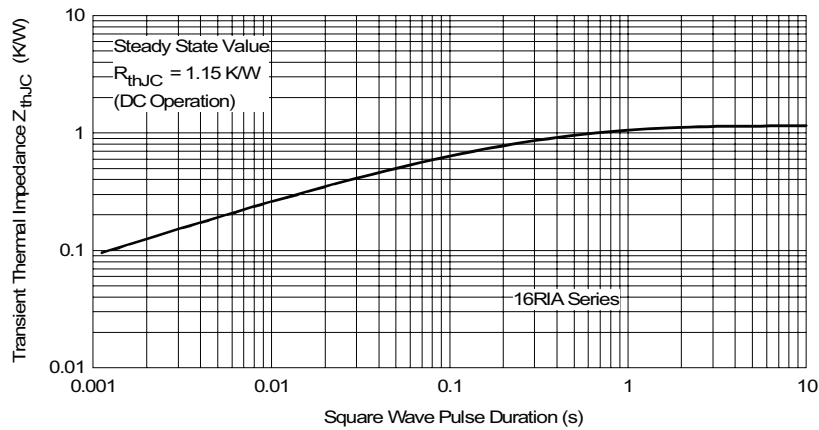


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

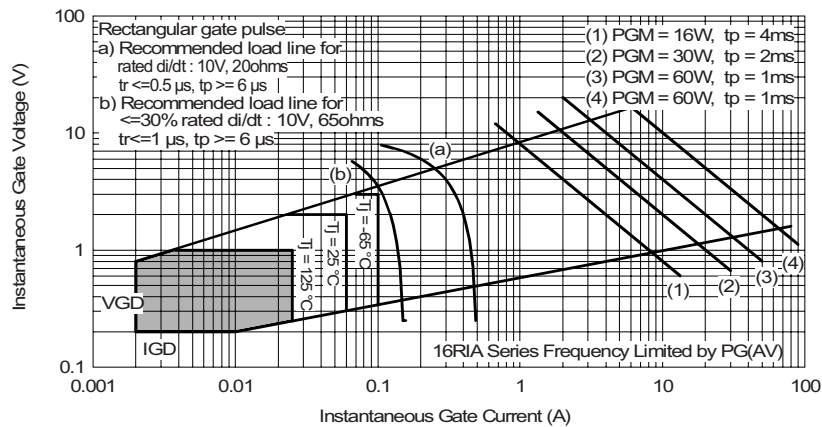


Fig. 9 - Gate Characteristics



ORDERING INFORMATION TABLE

Device code	16	RIA	120	M	S90
	1	2	3	4	5

- 1** - Current code
- 2** - Essential part number
- 3** - Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 4** - None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A
M = Stud base TO-208AA (TO-48) M6 x 1
- 5** - Critical dV/dt:
None = 300 V/ μ s (standard value)
S90 = 1000 V/ μ s (special selection)

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95333



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